



9N90

Power MOSFET

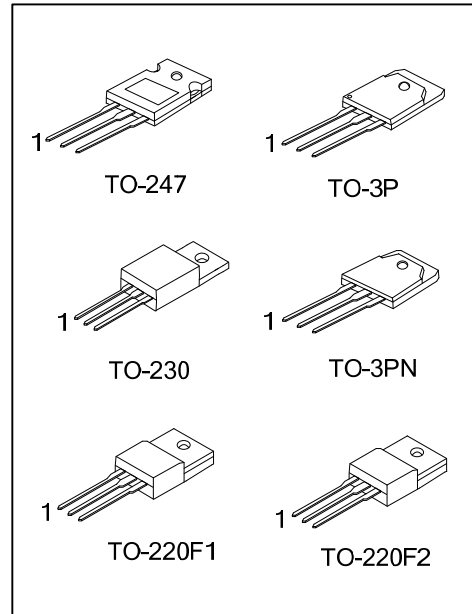
9A, 900V N-CHANNEL POWER MOSFET

DESCRIPTION

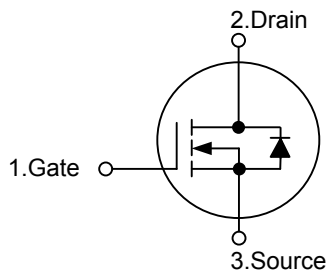
The UTC **9N90** uses UTC's advanced proprietary, planar stripe, DMOS technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with low gate voltages. This device is suitable for use as a load switch or in PWM applications.

FEATURES

- * $R_{DS(ON)} < 1.4\Omega$ @ $V_{GS} = 10V, I_D = 4.5A$
- * Ultra Low Gate Charge (Typical 45 nC)
- * Low Reverse Transfer Capacitance (CRSS = Typical 14 pF)
- * Fast Switching Capability
- * Avalanche Energy Specified
- * Improved dv/dt Capability, High Ruggedness



SYMBOL



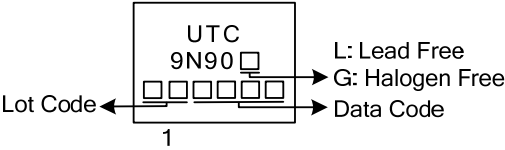
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
9N90L-T47-T	9N90G-T47-T	TO-247	G	D	S	Tube
9N90L-T3P-T	9N90G-T3P-T	TO-3P	G	D	S	Tube
9N90L-T3N-T	9N90G-T3N-T	TO-3PN	G	D	S	Tube
9N90L-TC3-T	9N90G-TC3-T	TO-230	G	D	S	Tube
9N90L-TF1-T	9N90G-TF1-T	TO-220F1	G	D	S	Tube
9N90L-TF2-T	9N90G-TF2-T	TO-220F2	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>9N90L-T47-T</p> <p>(1)Packing Type (2)Package Type (3)Green Package</p>	<p>(1) T: Tube (2) T47: TO-247, T3P: TO-3P, T3N: TO-3PN, TF1: TO-220F1, TF2: TO-220F2, TC3: TO-230 (3) L: Lead Free, G: Halogen Free and Lead Free</p>
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MARKING



■ ABSOLUTE MAXIMUM RATING ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	900	V
Gate-Source Voltage		V_{GSS}	± 30	V
Continuous Drain Current ($T_C = 25^\circ\text{C}$)		I_D	9.0	A
Pulsed Drain Current (Note 2)		I_{DM}	36	A
Avalanche Current (Note 2)		I_{AR}	9.0	A
Avalanche Energy	Single Pulsed(Note 3)	E_{AS}	900	mJ
	Repetitive(Note 2)	E_{AR}	28	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.0	V/ns
Power Dissipation	TO-247	P_D	160	W
	TO-3P/TO-3PN		240	W
	TO-230		147	
	TO-220F1		56	
	TO-220F2		58	
Linear Derating Factor above $T_C = 25^\circ\text{C}$	TO-247		1.28	
	TO-3P/TO-3PN		1.92	
	TO-230		1.176	
	TO-220F1		0.448	
	TO-220F2		0.464	
Junction Temperature		T_J	150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature

3. $L = 21\text{mH}$, $I_{AS} = 9.0\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 9.0\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-247	θ_{JA}	50	$^\circ\text{C}/\text{W}$
	TO-3P/TO-3PN		40	
	TO-220F1/ TO-220F2		62.5	
	TO-230			
Junction to Case	TO-247	θ_{JC}	0.78	$^\circ\text{C}/\text{W}$
	TO-3P/TO-3PN		0.52	
	TO-230		0.85	
	TO-220F1		2.25	
	TO-220F2		2.15	

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

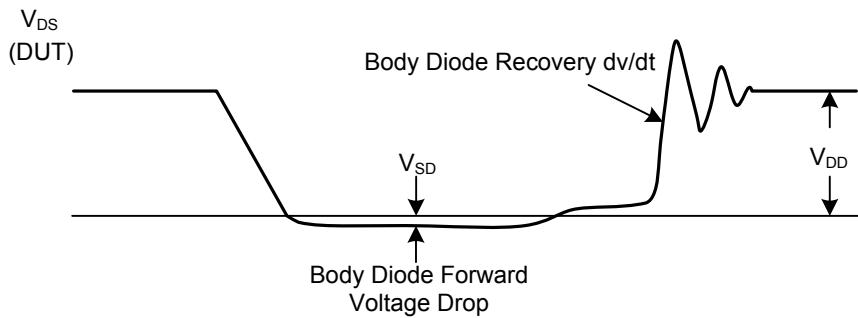
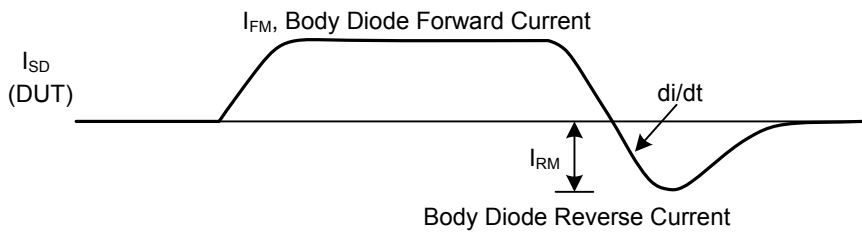
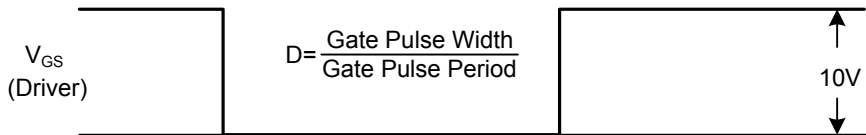
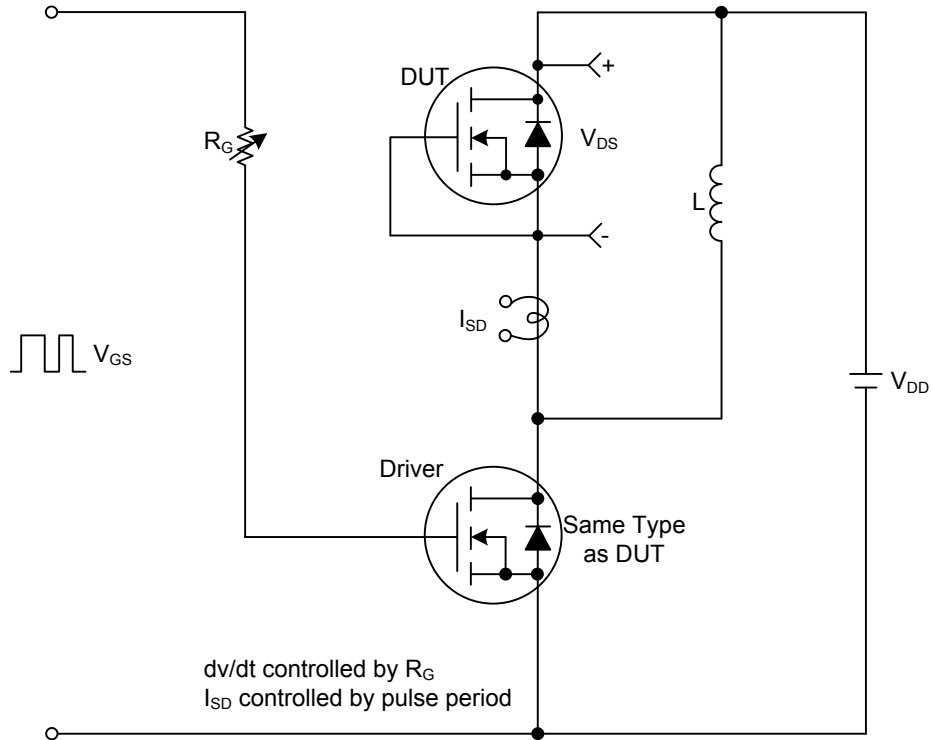
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0 V, I _D = 250μA	900			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} = 900 V, V _{GS} = 0 V			10	μA
Gate-Body Leakage Current	Forward	I _{GSSF}	V _{GS} = 30 V, V _{DS} = 0 V		100	nA
	Reverse	I _{GSSR}	V _{GS} = -30 V, V _{DS} = 0 V		-100	nA
Breakdown Voltage Temperature Coefficient	ΔBV _{DSS} /ΔT _J	I _D =250μA, Referenced to 25°C		0.99		V/°C
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} = V _{GS} , I _D = 250μA	3.0		5.0	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D = 4.5A		1.05	1.4	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C _{ISS}	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz		1870		pF
Output Capacitance	C _{OSS}			185		pF
Reverse Transfer Capacitance	C _{RSS}			21		pF
SWITCHING CHARACTERISTICS						
Total Gate Charge	Q _G	V _{DS} = 50V, V _{GS} = 10 V		215		nC
Gate-Source Charge	Q _{GS}	I _D = 1.3A, I _G = 100μA		17		nC
Gate-Drain Charge	Q _{GD}	(Note 1,2)		44		nC
Turn-On Delay Time	t _{D(ON)}	V _{DD} = 30V, V _{GS} = 10V, I _D = 0.5 A, R _G = 25Ω (Note 1, 2)		100		ns
Turn-On Rise Time	t _R			170		ns
Turn-Off Delay Time	t _{D(OFF)}			410		ns
Turn-Off Fall Time	t _F			175		ns
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Maximum Continuous Drain-Source Diode Forward Current	I _S				9.0	A
Maximum Pulsed Drain-Source Diode Forward Current	I _{SM}				36	A
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} = 0 V, I _S = 9.0 A			1.4	V
Reverse Recovery Time	t _{rr}	V _{GS} = 0 V, I _S = 9.0 A,		550		ns
Reverse Recovery Charge	Q _{RR}	dI _F / dt = 100 A/μs (Note 1)		6.5		μC

Notes: 1. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%

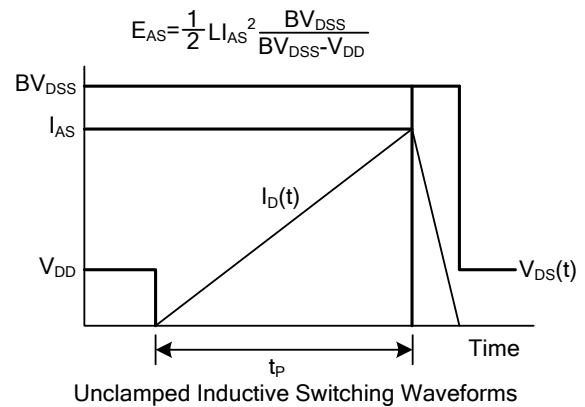
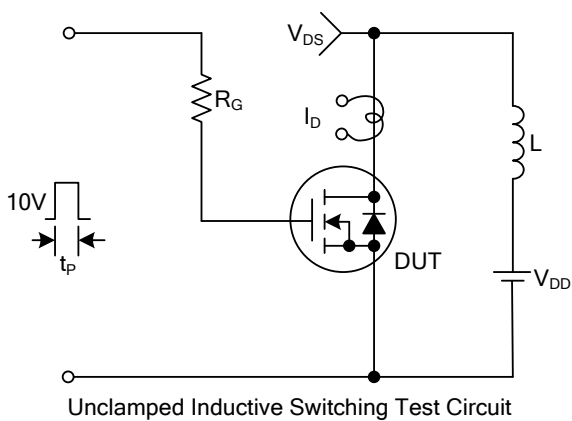
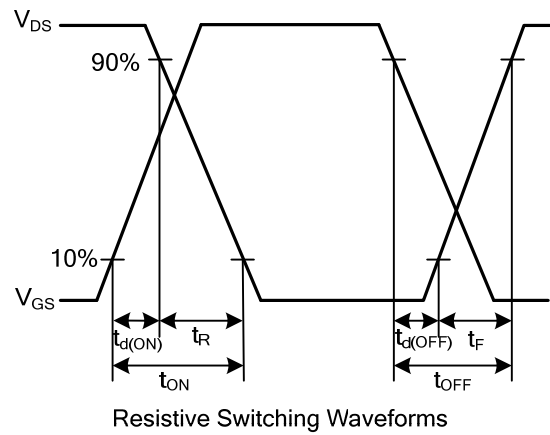
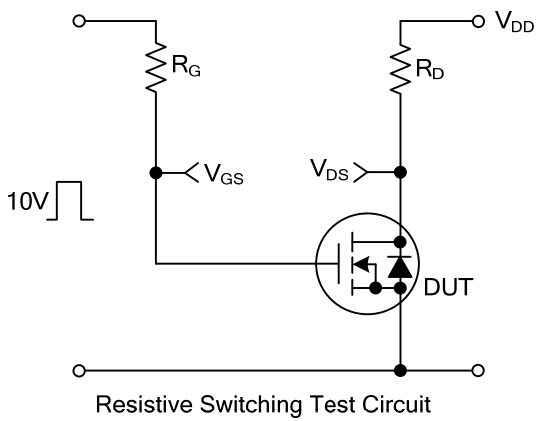
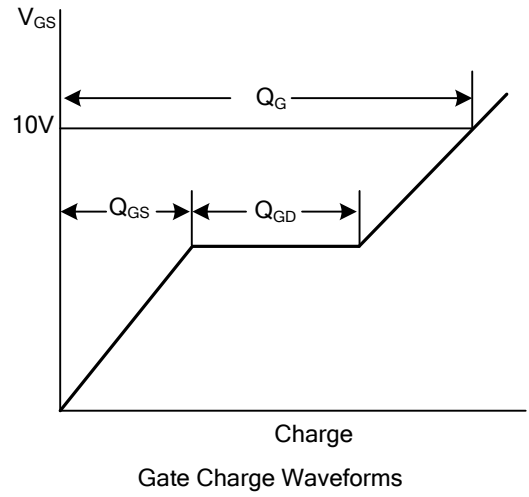
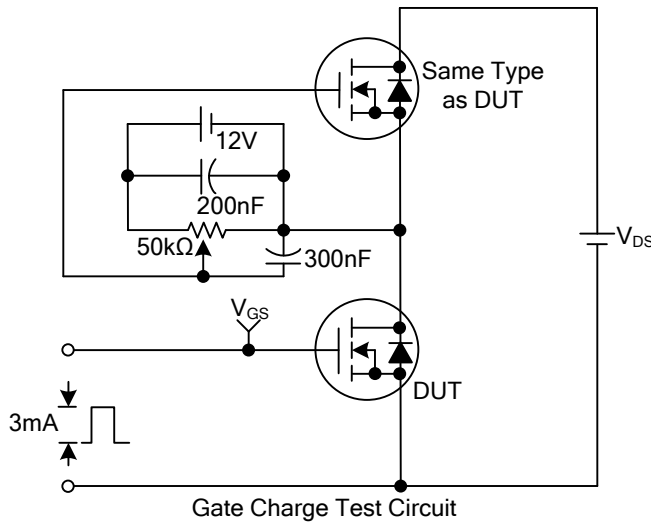
2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

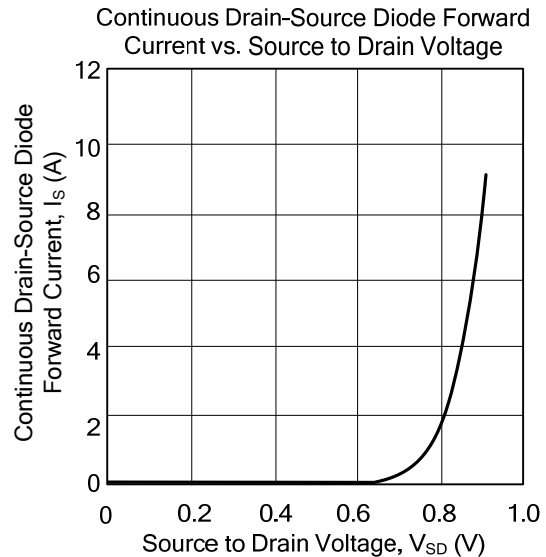
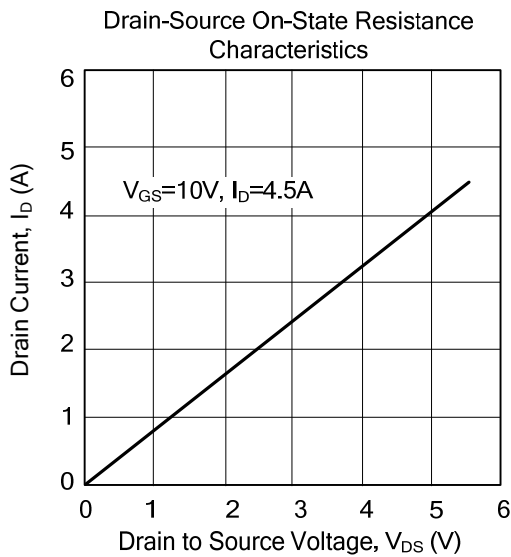
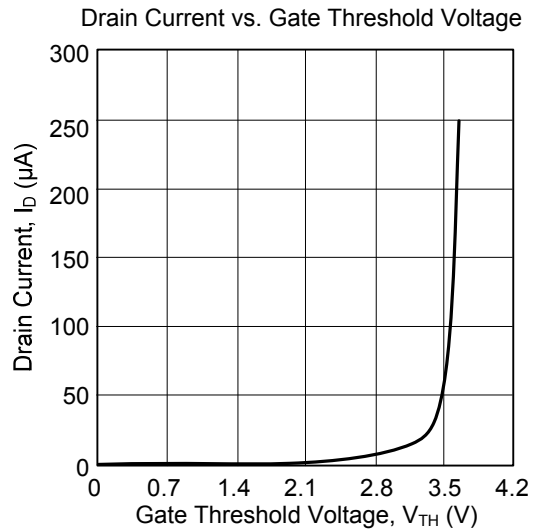
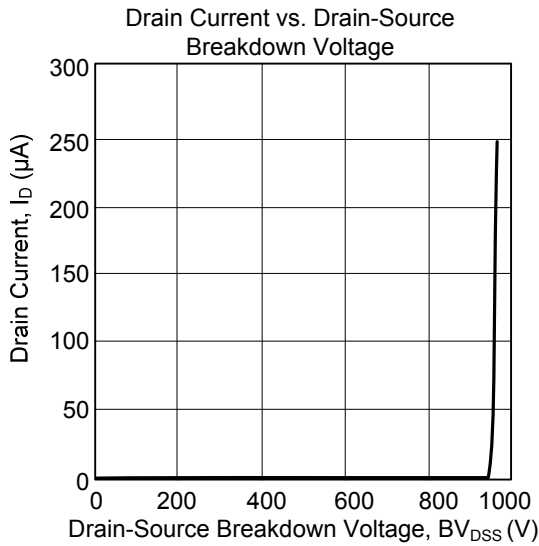
Peak Diode Recovery dv/dt Test Circuit & Waveforms



■ TEST CIRCUITS AND WAVEFORMS(Cont.)



■ TYPICAL CHARACTERISTICS



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